EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4113	(257/67,347,351).CCLS.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/18 10:24
L2	892	1 and (first second) adj (wafer substrate layer)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:25
L8	120	2 and ((first second) adj (wafer substrate layer)) near5 (bond bonding adhere adhering laminate laminating)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:31
L9	23	8 and ((first) adj (wafer substrate layer)) near5 (opening aperture groove trench via hole "through hole")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:31
L10	21	9 and (soi "buried oxide" "oxygen implant")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:32
L11	19	10 and @ad< "20040917"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:32
L12	7	11 and (nfet pfet "n-channel fet" "p-channel fet" cmos)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:33
L13	3155	(438/149,154,157).CCLS.	US-PGPUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/18 10:40
L14	773	13 and (first second) adj (wafer substrate layer)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:40
L16	116	14 and ((first second) adj (wafer substrate layer)) near5 (bond bonding adhere adhering laminate laminating stack stacked)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:41
L17	26	16 and ((first) adj (wafer substrate layer)) near5 (opening aperture groove trench via hole "through hole")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:41
L18	11	17 and (soi "buried oxide" "oxygen implant")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:42

L19	10	18 and @ad<"20040917"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:42
L20	4	19 and (nfet pfet "n-channel fet" "p-channel fet" cmos)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 10:42
L21	244945	(first second) adj (wafer substrate layer)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:01
L22	22842	21 and ((first second) adj (wafer substrate layer)) near5 (bond bonding adhere adhering laminate laminating stack stacked)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:01
L23	3429	22 and ((first) adj (wafer substrate layer)) near5 (opening aperture groove trench via hole "through hole")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:02
L24	331	23 and (soi "buried oxide" "oxygen implant")	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:02
L25	225	24 and @ad<"20040917"	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:02
L26	48	25 and (nfet pfet "n-channel fet" "p-channel fet" cmos)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:03
L29	21	25 and (opening aperture groove trench via hole "through hole") near5 (epitaxy epitaxial epitaxially)	US-PGPUB; USPAT; EPO; DERWENT	OR	ON	2007/12/18 11:05

12/18/07 11:21:35 AM
C:\Documents and Settings\wlouie\My Documents\EAST\Workspaces\FET.wsp